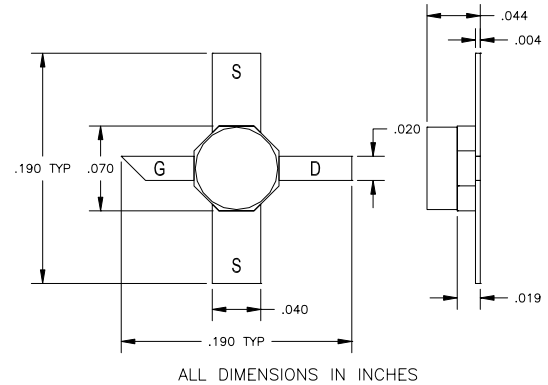


Low Distortion GaAs Power FET

FEATURES

- None-Hermetic Low Cost Ceramic 70mil Package
- +20.0 dBm Output Power at 1dB Compression
- 10.0 dB Power Gain at 12GHz
- 7.0 dB Power Gain at 18GHz
- Typical 1.50 dB Noise Figure and 10.0 dB Associated Gain at 12GHz
- 0.3 x 250 Micron Recessed "Mushroom" Gate
- Si₃N₄ Passivation
- Advanced Epitaxial Heterojunction Profile Provides High Power Efficiency, Linearity and Reliability



ELECTRICAL CHARACTERISTICS (T_a = 25°C)



Caution! ESD sensitive device.

| SYMBOL | PARAMETERS/TEST CONDITIONS ¹ | MIN | TYP | MAX | UNITS |
|------------------|---|------|--------------|------|-------|
| P _{1dB} | Output Power at 1dB Compression V _{DS} = 6V, I _{DS} ≈ 50% I _{DSS} f = 12GHz f = 18GHz | 17.0 | 20.0 20.0 | | dBm |
| G _{1dB} | Gain at 1dB Compression V _{DS} = 6V, I _{DS} ≈ 50% I _{DSS} f = 12GHz f = 18GHz | 8.5 | 10.0 7.0 | | dB |
| PAE | Power Added Efficiency at 1dB Compression V _{DS} = 6V, I _{DS} ≈ 50% I _{DSS} f = 12GHz | | 35 | | % |
| NF | Noise Figure V _{DS} = 3V, I _{DS} = 15mA f = 12GHz | | 1.5 | | dB |
| GA | Associate Gain V _{DS} = 3V, I _{DS} = 15mA f = 12GHz | | 10 | | dB |
| I _{DSS} | Saturated Drain Current V _{DS} = 3 V, V _{GS} = 0 V | 35 | 65 | 105 | mA |
| G _M | Transconductance V _{DS} = 3 V, V _{GS} = 0 V | 30 | 40 | | mS |
| V _P | Pinch-off Voltage V _{DS} = 3 V, I _{DS} = 1.0 mA | | -2.0 | -3.5 | V |
| BV _{GD} | Drain Breakdown Voltage I _{GD} = 1.0mA | -10 | -15 | | V |
| BV _{GS} | Source Breakdown Voltage I _{GS} = 1.0mA | -6 | -14 | | V |
| R _{TH} | Thermal Resistance | | 370* | | °C/W |

Notes: * Overall Rth depends on case mounting.

MAXIMUM RATINGS AT 25°C

| SYMBOL | CHARACTERISTIC | VALUE |
|------------------|-------------------------|-------------------|
| V _{DS} | Drain to Source Voltage | 6 V |
| V _{GS} | Gate to Source Voltage | -4 V |
| I _{DS} | Drain Current | 52 mA |
| I _{Gsf} | Forward Gate Current | 1 mA |
| P _{IN} | Input Power | @ 3dB compression |
| P _T | Total Power Dissipation | 310 mW |
| T _{CH} | Channel Temperature | 150°C |
| T _{STG} | Storage Temperature | -65/+150°C |

Note: 1. Exceeding any of the above ratings may result in permanent damage.
2. Exceeding any of the above ratings may reduce MTTF below design goals.

Specifications are subject to change without notice.



EFA025A-70

UPDATED 04/28/2006

Low Distortion GaAs Power FET

S-PARAMETERS

VDS = 3V, IDS ≈ 15mA

| FREQ (GHz) | --- S11 --- | | --- S21 --- | | --- S12 --- | | --- S22 --- | |
|---------------|-------------|--------|-------------|--------|-------------|--------|-------------|--------|
| | MAG | ANG | MAG | ANG | MAG | ANG | MAG | ANG |
| 1.0 | 1.020 | -17.0 | 4.385 | 159.6 | 0.030 | 75.6 | 0.549 | -22.5 |
| 2.0 | 0.956 | -37.8 | 3.291 | 142.6 | 0.043 | 64.4 | 0.611 | -28.0 |
| 3.0 | 0.911 | -56.4 | 3.114 | 125.5 | 0.060 | 52.4 | 0.601 | -41.2 |
| 4.0 | 0.867 | -73.0 | 2.944 | 109.6 | 0.072 | 42.4 | 0.577 | -52.4 |
| 5.0 | 0.814 | -89.2 | 2.856 | 93.8 | 0.084 | 32.3 | 0.535 | -63.9 |
| 6.0 | 0.748 | -105.5 | 2.697 | 78.2 | 0.089 | 22.3 | 0.514 | -78.5 |
| 7.0 | 0.689 | -124.2 | 2.523 | 64.0 | 0.092 | 14.6 | 0.511 | -85.8 |
| 8.0 | 0.656 | -144.7 | 2.424 | 49.6 | 0.096 | 6.5 | 0.489 | -92.9 |
| 9.0 | 0.636 | -151.0 | 2.334 | 36.0 | 0.098 | -2.9 | 0.384 | -111.2 |
| 10.0 | 0.584 | -166.5 | 2.283 | 21.7 | 0.096 | -4.4 | 0.390 | -131.4 |
| 11.0 | 0.545 | 164.8 | 2.150 | 7.2 | 0.095 | -10.8 | 0.432 | -132.6 |
| 12.0 | 0.552 | 142.3 | 2.040 | -5.8 | 0.095 | -15.2 | 0.409 | -133.6 |
| 13.0 | 0.589 | 134.6 | 1.982 | -20.5 | 0.102 | -21.4 | 0.351 | -168.6 |
| 14.0 | 0.563 | 120.6 | 1.877 | -36.0 | 0.100 | -31.0 | 0.371 | 162.5 |
| 15.0 | 0.571 | 96.0 | 1.672 | -50.1 | 0.096 | -35.6 | 0.387 | 166.7 |
| 16.0 | 0.607 | 73.2 | 1.625 | -63.4 | 0.098 | -41.9 | 0.374 | 168.3 |
| 17.0 | 0.625 | 77.3 | 1.617 | -78.1 | 0.108 | -49.6 | 0.392 | 116.3 |
| 18.0 | 0.618 | 58.5 | 1.411 | -92.5 | 0.105 | -58.9 | 0.476 | 108.4 |
| 19.0 | 0.643 | 42.1 | 1.361 | -102.2 | 0.109 | -68.8 | 0.428 | 110.5 |
| 20.0 | 0.691 | 26.8 | 1.329 | -116.0 | 0.103 | -80.6 | 0.411 | 101.9 |
| 21.0 | 0.653 | 22.4 | 1.294 | -135.8 | 0.105 | -95.7 | 0.539 | 62.8 |
| 22.0 | 0.634 | 13.4 | 1.160 | -146.5 | 0.103 | -105.5 | 0.620 | 64.2 |
| 23.0 | 0.655 | -8.1 | 1.172 | -161.2 | 0.110 | -120.8 | 0.479 | 61.0 |
| 24.0 | 0.646 | -25.3 | 1.170 | 178.6 | 0.119 | -141.1 | 0.478 | 34.5 |
| 25.0 | 0.563 | -39.9 | 1.074 | 160.7 | 0.118 | -159.4 | 0.624 | 17.3 |
| 26.0 | 0.596 | -47.4 | 1.048 | 149.8 | 0.132 | -169.1 | 0.562 | 15.8 |

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 Revised May 2006



EFA025A-70

UPDATED 04/28/2006

Low Distortion GaAs Power FET

S-PARAMETERS

VDS = 3V, IDS ≈ ½ Idss

| FREQ (GHz) | --- S11 --- | | --- S21 --- | | --- S12 --- | | --- S22 --- | |
|---------------|-------------|--------|-------------|--------|-------------|--------|-------------|--------|
| | MAG | ANG | MAG | ANG | MAG | ANG | MAG | ANG |
| 1.0 | 0.985 | -18.8 | 3.482 | 161.4 | 0.013 | 76.6 | 0.803 | -11.3 |
| 2.0 | 0.953 | -38 | 3.329 | 142.7 | 0.025 | 65.9 | 0.786 | -24.1 |
| 3.0 | 0.913 | -56 | 3.108 | 125.5 | 0.031 | 54.2 | 0.768 | -36 |
| 4.0 | 0.872 | -73.2 | 2.97 | 109.5 | 0.037 | 46.2 | 0.755 | -45.6 |
| 5.0 | 0.825 | -89.3 | 2.867 | 94.3 | 0.04 | 38.8 | 0.731 | -54.5 |
| 6.0 | 0.779 | -102.7 | 2.713 | 79.7 | 0.04 | 34.4 | 0.703 | -66.2 |
| 7.0 | 0.734 | -117.1 | 2.559 | 65.3 | 0.039 | 30.9 | 0.685 | -76.8 |
| 8.0 | 0.688 | -130.5 | 2.448 | 52.1 | 0.033 | 33.5 | 0.66 | -85.6 |
| 9.0 | 0.642 | -152.3 | 2.42 | 37.6 | 0.037 | 44.6 | 0.661 | -91.4 |
| 10.0 | 0.614 | -173.2 | 2.355 | 21.8 | 0.044 | 48.1 | 0.654 | -102.2 |
| 11.0 | 0.591 | 177.4 | 2.312 | 8.6 | 0.054 | 50.4 | 0.642 | -117.7 |
| 12.0 | 0.572 | 163.7 | 2.282 | -5.4 | 0.071 | 50.2 | 0.641 | -131.9 |
| 13.0 | 0.598 | 138.2 | 2.188 | -22 | 0.086 | 40.5 | 0.638 | -144.4 |
| 14.0 | 0.631 | 115.4 | 2.036 | -38.8 | 0.097 | 29.4 | 0.642 | -158.9 |
| 15.0 | 0.631 | 102.2 | 1.97 | -54.9 | 0.112 | 18.3 | 0.667 | 179.8 |
| 16.0 | 0.634 | 87.3 | 1.909 | -72.4 | 0.126 | 5.6 | 0.685 | 158.4 |
| 17.0 | 0.658 | 70.3 | 1.685 | -87.7 | 0.128 | -2.1 | 0.665 | 145.1 |
| 18.0 | 0.694 | 59 | 1.58 | -99.5 | 0.15 | -17.2 | 0.731 | 132.5 |
| 19.0 | 0.672 | 42 | 1.467 | -116.1 | 0.137 | -30.5 | 0.761 | 113.1 |
| 20.0 | 0.707 | 25.5 | 1.399 | -132.9 | 0.143 | -43.3 | 0.836 | 96.6 |
| 21.0 | 0.761 | 14.9 | 1.29 | -148.4 | 0.143 | -56.3 | 0.826 | 84.7 |
| 22.0 | 0.736 | 3.9 | 1.184 | -161.3 | 0.138 | -68.7 | 0.83 | 76 |
| 23.0 | 0.703 | -15.3 | 1.103 | -178.5 | 0.134 | -84.6 | 0.824 | 58.8 |
| 24.0 | 0.723 | -33.5 | 1.043 | 162.6 | 0.134 | -101.6 | 0.841 | 41.2 |
| 25.0 | 0.705 | -44.7 | 1.017 | 146.3 | 0.14 | -117.8 | 0.843 | 28.4 |
| 26.0 | 0.676 | -59.8 | 1.017 | 131.8 | 0.156 | -131 | 0.831 | 16.6 |

NOISE-PARAMETERS

VDS = 3V, IDS ≈ 15mA

| FREQ (GHz) | Gamma Opt | | Nfmin (dB) | Rn/50 |
|---------------|-----------|------|---------------|-------|
| | MAG | ANG | | |
| 2 | 0.83 | 28 | 0.53 | 0.58 |
| 4 | 0.75 | 59 | 0.65 | 0.48 |
| 6 | 0.65 | 85 | 0.85 | 0.33 |
| 8 | 0.58 | 128 | 1.05 | 0.21 |
| 10 | 0.45 | 147 | 1.35 | 0.11 |
| 12 | 0.40 | -170 | 1.55 | 0.10 |
| 14 | 0.41 | -111 | 1.90 | 0.27 |
| 16 | 0.47 | -69 | 2.25 | 0.58 |
| 18 | 0.53 | -44 | 2.60 | 1.00 |
| 20 | 0.62 | -14 | 2.90 | 1.38 |
| 22 | 0.57 | 1 | 3.20 | 1.68 |
| 24 | 0.59 | 39 | 3.50 | 1.77 |
| 26 | 0.57 | 66 | 3.80 | 1.10 |

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 Revised May 2006